

Adam Gali

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

309
papers

9,799
citations

51
h-index

85
g-index

329
ext. papers

11,348
ext. citations

5
avg. IF

6.55
L-index

#	Paper	IF	Citations
309	Ultra-high nitrogen-vacancy center concentration in diamond. <i>Carbon</i> , 2022 , 188, 393-400	10.4	1
308	Photoluminescence spectrum of divacancy in porous and nanocrystalline cubic silicon carbide. <i>Journal of Applied Physics</i> , 2022 , 131, 071102	2.5	3
307	Carbon defect qubit in two-dimensional WS ₂ . <i>Nature Communications</i> , 2022 , 13, 1210	17.4	2
306	Ultraviolet Quantum Emitters in Hexagonal Boron Nitride from Carbon Clusters. <i>Journal of Physical Chemistry Letters</i> , 2022 , 3150-3157	6.4	2
305	Strong Zero-Phonon Transition from Point Defect-Stacking Fault Complexes in Silicon Carbide Nanowires. <i>Nano Letters</i> , 2021 , 21, 9187-9194	11.5	1
304	Identification of a Telecom Wavelength Single Photon Emitter in Silicon. <i>Physical Review Letters</i> , 2021 , 127, 196402	7.4	6
303	Structure and Properties of Heavily B and P Codoped Amorphous Silicon Quantum Dots. <i>Journal of Physical Chemistry C</i> , 2021 , 125, 23267-23274	3.8	
302	Point Defects in Silicon Carbide for Quantum Technology 2021 , 503-528		1
301	Enhancement of X-ray-Excited Red Luminescence of Chromium-Doped Zinc Gallate via Ultrasmall Silicon Carbide Nanocrystals. <i>Chemistry of Materials</i> , 2021 , 33, 2457-2465	9.6	2
300	Robust coherent control of solid-state spin qubits using anti-Stokes excitation. <i>Nature Communications</i> , 2021 , 12, 3223	17.4	5
299	Single-spin resonance in a van der Waals embedded paramagnetic defect. <i>Nature Materials</i> , 2021 , 20, 1079-1084	27	27
298	Highly tunable magneto-optical response from magnesium-vacancy color centers in diamond. <i>Npj Quantum Information</i> , 2021 , 7,	8.6	4
297	Room-temperature control and electrical readout of individual nitrogen-vacancy nuclear spins. <i>Nature Communications</i> , 2021 , 12, 4421	17.4	8
296	Fundamentals of photoelectric readout of spin states in diamond. <i>Semiconductors and Semimetals</i> , 2021 , 105-147	0.6	2
295	Solar Photoelectroreduction of Nitrate Ions on PbI ₂ /CuI Nanocomposite Electrodes. <i>Solar Rrl</i> , 2021 , 5, 2000418	7.1	1
294	Photoluminescence at the ground-state level anticrossing of the nitrogen-vacancy center in diamond: A comprehensive study. <i>Physical Review B</i> , 2021 , 103,	3.3	6
293	Towards identification of silicon vacancy-related electron paramagnetic resonance centers in 4H-SiC. <i>Physical Review B</i> , 2021 , 104,	3.3	4

292	Towards ab initio identification of paramagnetic substitutional carbon defects in hexagonal boron nitride acting as quantum bits. <i>Physical Review B</i> , 2021 , 104,	3.3	6
291	DMRG on Top of Plane-Wave Kohn-Sham Orbitals: A Case Study of Defected Boron Nitride. <i>Journal of Chemical Theory and Computation</i> , 2021 , 17, 1143-1154	6.4	9
290	Silicon-Carbide (SiC) Nanocrystal Technology and Characterization and Its Applications in Memory Structures. <i>Nanomaterials</i> , 2020 , 10,	5.4	2
289	Ab initio theory of the negatively charged boron vacancy qubit in hexagonal boron nitride. <i>Npj Computational Materials</i> , 2020 , 6,	10.9	55
288	Vibronic States and Their Effect on the Temperature and Strain Dependence of Silicon-Vacancy Qubits in 4H-SiC. <i>Physical Review Applied</i> , 2020 , 13,	4.3	29
287	Interlayer Bonding in Two-Dimensional Materials: The Special Case of SnP and GeP. <i>Journal of Physical Chemistry Letters</i> , 2020 , 11, 4503-4510	6.4	12
286	Spin-controlled generation of indistinguishable and distinguishable photons from silicon vacancy centres in silicon carbide. <i>Nature Communications</i> , 2020 , 11, 2516	17.4	24
285	Room-temperature coherent control of implanted defect spins in silicon carbide. <i>Npj Quantum Information</i> , 2020 , 6,	8.6	5
284	Novel Method for Electroless Etching of 6H-SiC. <i>Nanomaterials</i> , 2020 , 10,	5.4	4
283	Room-Temperature Defect Qubits in Ultrasmall Nanocrystals. <i>Journal of Physical Chemistry Letters</i> , 2020 , 11, 1675-1681	6.4	11
282	Immunomodulatory Potential of Differently-Terminated Ultra-Small Silicon Carbide Nanoparticles. <i>Nanomaterials</i> , 2020 , 10,	5.4	3
281	Thermal evolution of silicon carbide electronic bands. <i>Physical Review Materials</i> , 2020 , 4,	3.2	4
280	Color centers in diamond for quantum applications. <i>Semiconductors and Semimetals</i> , 2020 , 1-36	0.6	2
279	Spectroscopic investigations of negatively charged tin-vacancy centres in diamond. <i>New Journal of Physics</i> , 2020 , 22, 013048	2.9	32
278	Theoretical study of quantum emitters in two-dimensional silicon carbide monolayers. <i>Physical Review B</i> , 2020 , 102,	3.3	3
277	Giant shift upon strain on the fluorescence spectrum of VNNB color centers in h-BN. <i>Npj Quantum Information</i> , 2020 , 6,	8.6	12
276	Material platforms for defect qubits and single-photon emitters. <i>Applied Physics Reviews</i> , 2020 , 7, 031308	8.3	37
275	Stone-Wales defects in hexagonal boron nitride as ultraviolet emitters. <i>Npj Computational Materials</i> , 2020 , 6,	10.9	11

274	Ab initio determination of pseudospin for paramagnetic defects in SiC. <i>Physical Review B</i> , 2020 , 102,	3.3	6
273	Optically Detected Magnetic Resonance in Neutral Silicon Vacancy Centers in Diamond via Bound Exciton States. <i>Physical Review Letters</i> , 2020 , 125, 237402	7.4	17
272	Electrical Charge State Manipulation of Single Silicon Vacancies in a Silicon Carbide Quantum Optoelectronic Device. <i>Nano Letters</i> , 2019 , 19, 7173-7180	11.5	36
271	Oxygenated (113) diamond surface for nitrogen-vacancy quantum sensors with preferential alignment and long coherence time from first principles. <i>Carbon</i> , 2019 , 145, 273-280	10.4	13
270	High-fidelity spin and optical control of single silicon-vacancy centres in silicon carbide. <i>Nature Communications</i> , 2019 , 10, 1954	17.4	99
269	Identification of divacancy and silicon vacancy qubits in 6H-SiC. <i>Applied Physics Letters</i> , 2019 , 114, 112103	3.4	15
268	Spectrally Stable Defect Qubits with no Inversion Symmetry for Robust Spin-To-Photon Interface. <i>Physical Review Applied</i> , 2019 , 11,	4.3	26
267	Size-Dependent Photocatalytic Activity of Cubic Boron Phosphide Nanocrystals in the Quantum Confinement Regime. <i>Journal of Physical Chemistry C</i> , 2019 , 123, 23226-23235	3.8	6
266	Optical Properties of Vanadium in 4H Silicon Carbide for Quantum Technology. <i>Physical Review Applied</i> , 2019 , 12,	4.3	32
265	Optically Active Defects at the SiC/SiO ₂ Interface. <i>Physical Review Applied</i> , 2019 , 12,	4.3	10
264	The (eg ? eu) ? Eg product Jahn-Teller effect in the neutral group-IV vacancy quantum bits in diamond. <i>Npj Computational Materials</i> , 2019 , 5,	10.9	23
263	Ab initio theory of the nitrogen-vacancy center in diamond. <i>Nanophotonics</i> , 2019 , 8, 1907-1943	6.3	65
262	First-Principles Study on Photoluminescence Quenching of Divacancy in 4H SiC. <i>Materials Science Forum</i> , 2019 , 963, 714-717	0.4	1
261	Stabilization of point-defect spin qubits by quantum wells. <i>Nature Communications</i> , 2019 , 10, 5607	17.4	28
260	Electrically driven optical interferometry with spins in silicon carbide. <i>Science Advances</i> , 2019 , 5, eaay05274	4.3	31
259	Evidence for Primal sp ² Defects at the Diamond Surface: Candidates for Electron Trapping and Noise Sources. <i>Advanced Materials Interfaces</i> , 2019 , 6, 1801449	4.6	40
258	Color Centers in Hexagonal Boron Nitride Monolayers: A Group Theory and Ab Initio Analysis. <i>ACS Photonics</i> , 2018 , 5, 1967-1976	6.3	100
257	First principles predictions of magneto-optical data for semiconductor point defect identification: the case of divacancy defects in 4H SiC. <i>New Journal of Physics</i> , 2018 , 20, 023035	2.9	25

256	Identification of the binding site between bovine serum albumin and ultrasmall SiC fluorescent biomarkers. <i>Physical Chemistry Chemical Physics</i> , 2018 , 20, 13419-13429	3.6	10
255	Room temperature solid-state quantum emitters in the telecom range. <i>Science Advances</i> , 2018 , 4, earr3580	3.4	63
254	First-Principles Study of Charge Diffusion between Proximate Solid-State Qubits and Its Implications on Sensor Applications. <i>Physical Review Letters</i> , 2018 , 120, 136401	7.4	12
253	Spin-strain interaction in nitrogen-vacancy centers in diamond. <i>Physical Review B</i> , 2018 , 98,	3.3	50
252	Vibrational modes of negatively charged silicon-vacancy centers in diamond from ab initio calculations. <i>Physical Review B</i> , 2018 , 98,	3.3	20
251	Vibrational relaxation dynamics of the nitrogen-vacancy center in diamond. <i>Physical Review B</i> , 2018 , 97,	3.3	13
250	Ab initio description of highly correlated states in defects for realizing quantum bits. <i>Npj Quantum Materials</i> , 2018 , 3,	5	38
249	Ab Initio Magneto-Optical Spectrum of Group-IV Vacancy Color Centers in Diamond. <i>Physical Review X</i> , 2018 , 8,	9.1	61
248	Strongly inhomogeneous distribution of spectral properties of silicon-vacancy color centers in nanodiamonds. <i>New Journal of Physics</i> , 2018 , 20, 115002	2.9	27
247	Ab Initio Spin-Strain Coupling Parameters of Divacancy Qubits in Silicon Carbide. <i>Physical Review Applied</i> , 2018 , 10,	4.3	15
246	Excitation properties of the divacancy in 4H-SiC. <i>Physical Review B</i> , 2018 , 98,	3.3	33
245	Strongly anisotropic spin relaxation in the neutral silicon vacancy center in diamond. <i>Physical Review B</i> , 2018 , 98,	3.3	13
244	First principles calculation of spin-related quantities for point defect qubit research. <i>Npj Computational Materials</i> , 2018 , 4,	10.9	31
243	Photoluminescence, infrared, and Raman spectra of co-doped Si nanoparticles from first principles. <i>Journal of Chemical Physics</i> , 2018 , 149, 154702	3.9	5
242	Direct Observation of Transition from Solid-State to Molecular-Like Optical Properties in Ultrasmall Silicon Carbide Nanoparticles. <i>Journal of Physical Chemistry C</i> , 2018 , 122, 26713-26721	3.8	5
241	Theory of the optical spin-polarization loop of the nitrogen-vacancy center in diamond. <i>Physical Review B</i> , 2018 , 98,	3.3	35
240	Identification of nickel-vacancy defects by combining experimental and ab initio simulated photocurrent spectra. <i>Physical Review B</i> , 2018 , 97,	3.3	14
239	Ab Initio Theory of Si-Vacancy Quantum Bits in 4H and 6H-SiC. <i>Materials Science Forum</i> , 2018 , 924, 895-900	4	1

238	Enhanced photoelectric detection of NV magnetic resonances in diamond under dual-beam excitation. <i>Physical Review B</i> , 2017 , 95,	3.3	25
237	Bright Room-Temperature Single-Photon Emission from Defects in Gallium Nitride. <i>Advanced Materials</i> , 2017 , 29, 1605092	24	66
236	Nitrogen-Terminated Diamond (111) Surface for Room-Temperature Quantum Sensing and Simulation. <i>Nano Letters</i> , 2017 , 17, 2294-2298	11.5	48
235	Optical Gaps in Pristine and Heavily Doped Silicon Nanocrystals: DFT versus Quantum Monte Carlo Benchmarks. <i>Journal of Chemical Theory and Computation</i> , 2017 , 13, 6061-6067	6.4	8
234	Density Functional Theory on NV Center in 4H SiC. <i>Materials Science Forum</i> , 2017 , 897, 269-274	0.4	1
233	Hybrid-DFT + V method for band structure calculation of semiconducting transition metal compounds: the case of cerium dioxide. <i>Journal of Physics Condensed Matter</i> , 2017 , 29, 454002	1.8	5
232	Ab initio calculation of spin-orbit coupling for an NV center in diamond exhibiting dynamic Jahn-Teller effect. <i>Physical Review B</i> , 2017 , 96,	3.3	46
231	Protecting a Diamond Quantum Memory by Charge State Control. <i>Nano Letters</i> , 2017 , 17, 5931-5937	11.5	51
230	Characterization and formation of NV centers in 3C, 4H, and 6H SiC: An ab initio study. <i>Physical Review B</i> , 2017 , 96,	3.3	38
229	Harnessing no-photon exciton generation chemistry to engineer semiconductor nanostructures. <i>Scientific Reports</i> , 2017 , 7, 10599	4.9	11
228	Nitrogen-vacancy diamond sensor: novel diamond surfaces from ab initio simulations. <i>MRS Communications</i> , 2017 , 7, 551-562	2.7	17
227	All-optical hyperpolarization of electron and nuclear spins in diamond. <i>Physical Review B</i> , 2017 , 96,	3.3	9
226	Surface-Mediated Energy Transfer and Subsequent Photocatalytic Behavior in Silicon Carbide Colloid Solutions. <i>Langmuir</i> , 2017 , 33, 14263-14268	4	5
225	High-Throughput Study of Compositions and Optical Properties in Heavily Co-Doped Silicon Nanoparticles. <i>Journal of Physical Chemistry C</i> , 2017 , 121, 27741-27750	3.8	10
224	Ab initio theory of the N2V defect in diamond for quantum memory implementation. <i>Physical Review B</i> , 2017 , 96,	3.3	6
223	Identification of Si-vacancy related room-temperature qubits in 4H silicon carbide. <i>Physical Review B</i> , 2017 , 96,	3.3	51
222	Pulsed Photoelectric Coherent Manipulation and Detection of NV Center Spins in Diamond. <i>Physical Review Applied</i> , 2017 , 7,	4.3	20
221	Publisher's Note: Pulsed Photoelectric Coherent Manipulation and Detection of NV Center Spins in Diamond [Phys. Rev. Applied 7, 044032 (2017)]. <i>Physical Review Applied</i> , 2017 , 7,	4.3	3

220	Isolated Spin Qubits in SiC with a High-Fidelity Infrared Spin-to-Photon Interface. <i>Physical Review X</i> , 2017 , 7,	9.1	78
219	Photoluminescence excitation spectroscopy of SiV and GeV color center in diamond. <i>New Journal of Physics</i> , 2017 , 19, 063036	2.9	51
218	High-Fidelity Bidirectional Nuclear Qubit Initialization in SiC. <i>Physical Review Letters</i> , 2016 , 117, 220503	7.4	13
217	Characterization of oxygen defects in diamond by means of density functional theory calculations. <i>Physical Review B</i> , 2016 , 94,	3.3	14
216	Microscopic modeling of the effect of phonons on the optical properties of solid-state emitters. <i>Physical Review B</i> , 2016 , 94,	3.3	14
215	First Principles Identification of Divacancy Related Photoluminescence Lines in 4H and 6H-SiC. <i>Materials Science Forum</i> , 2016 , 858, 322-325	0.4	1
214	Determination of silicon and aluminum in silicon carbide nanocrystals by high-resolution continuum source graphite furnace atomic absorption spectrometry. <i>Talanta</i> , 2016 , 147, 271-5	6.2	12
213	Identification of Luminescence Centers in Molecular-Sized Silicon Carbide Nanocrystals. <i>Journal of Physical Chemistry C</i> , 2016 , 120, 685-691	3.8	26
212	Investigation of Mo Defects in 4H-SiC by Means of Density Functional Theory. <i>Materials Science Forum</i> , 2016 , 858, 261-264	0.4	4
211	Electron-vibration coupling induced renormalization in the photoemission spectrum of diamondoids. <i>Nature Communications</i> , 2016 , 7, 11327	17.4	31
210	Engineering Single Defects in Silicon Carbide Bulk, Nanostructures and Devices. <i>Materials Science Forum</i> , 2016 , 858, 312-317	0.4	2
209	NV centers in 3C,4H, and 6H silicon carbide: A variable platform for solid-state qubits and nanosensors. <i>Physical Review B</i> , 2016 , 94,	3.3	59
208	Optically detected magnetic resonances of nitrogen-vacancy ensembles in C13-enriched diamond. <i>Physical Review B</i> , 2016 , 94,	3.3	4
207	Optical Polarization of Nuclear Spins in Silicon Carbide. <i>Physical Review Letters</i> , 2015 , 114, 247603	7.4	86
206	Spin and photophysics of carbon-antisite vacancy defect in 4H silicon carbide: A potential quantum bit. <i>Physical Review B</i> , 2015 , 91,	3.3	41
205	Single-photon emitting diode in silicon carbide. <i>Nature Communications</i> , 2015 , 6, 7783	17.4	129
204	Coherent control of single spins in silicon carbide at room temperature. <i>Nature Materials</i> , 2015 , 14, 164-87	8.7	347
203	Optical properties and Zeeman spectroscopy of niobium in silicon carbide. <i>Physical Review B</i> , 2015 , 92,	3.3	5

202	Complexes of silicon, vacancy, and hydrogen in diamond: A density functional study. <i>Physical Review B</i> , 2015 , 92,	3.3	22
201	Nitrogen Terminated Diamond. <i>Advanced Materials Interfaces</i> , 2015 , 2, 1500079	4.6	47
200	Dominant luminescence is not due to quantum confinement in molecular-sized silicon carbide nanocrystals. <i>Nanoscale</i> , 2015 , 7, 10982-8	7.7	37
199	Theoretical model of dynamic spin polarization of nuclei coupled to paramagnetic point defects in diamond and silicon carbide. <i>Physical Review B</i> , 2015 , 92,	3.3	47
198	Theoretical and electron paramagnetic resonance studies of hyperfine interaction in nitrogen doped 4H and 6H SiC. <i>Journal of Applied Physics</i> , 2014 , 115, 073705	2.5	16
197	Molecular-sized fluorescent nanodiamonds. <i>Nature Nanotechnology</i> , 2014 , 9, 54-8	28.7	185
196	A silicon carbide room-temperature single-photon source. <i>Nature Materials</i> , 2014 , 13, 151-6	27	349
195	Optoelectronic excitations and photovoltaic effect in strongly correlated materials. <i>Physical Review B</i> , 2014 , 90,	3.3	20
194	First principles study of point defects in SnS. <i>Physical Chemistry Chemical Physics</i> , 2014 , 16, 26176-83	3.6	60
193	Germanium nanoparticles with non-diamond core structures for solar energy conversion. <i>Journal of Materials Chemistry A</i> , 2014 , 2, 9820	13	25
192	Room temperature quantum emission from cubic silicon carbide nanoparticles. <i>ACS Nano</i> , 2014 , 8, 7938-47	46.7	77
191	Proper surface termination for luminescent near-surface NV centers in diamond. <i>Nano Letters</i> , 2014 , 14, 4772-7	11.5	92
190	Theoretical unification of hybrid-DFT and DFT + U methods for the treatment of localized orbitals. <i>Physical Review B</i> , 2014 , 90,	3.3	36
189	Formation of NV centers in diamond: A theoretical study based on calculated transitions and migration of nitrogen and vacancy related defects. <i>Physical Review B</i> , 2014 , 89,	3.3	113
188	Fluorine Modification of the Surface of Diamondoids: A Time-Dependent Density Functional Study. <i>Journal of Physical Chemistry C</i> , 2014 , 118, 4410-4415	3.8	12
187	Single nickel-related defects in molecular-sized nanodiamonds for multicolor bioimaging: an ab initio study. <i>Nanoscale</i> , 2014 , 6, 12018-25	7.7	15
186	Solar nanocomposites with complementary charge extraction pathways for electrons and holes: Si embedded in ZnS. <i>Physical Review Letters</i> , 2014 , 112, 106801	7.4	19
185	Quantum-confined single photon emission at room temperature from SiC tetrapods. <i>Nanoscale</i> , 2014 , 6, 10027-32	7.7	17

184	Computational design of in vivo biomarkers. <i>Journal of Physics Condensed Matter</i> , 2014 , 26, 143202	1.8	11
183	The spin-spin zero-field splitting tensor in the projector-augmented-wave method. <i>Journal of Physics Condensed Matter</i> , 2014 , 26, 015305	1.8	20
182	Chemical Transformation of Carboxyl Groups on the Surface of Silicon Carbide Quantum Dots. <i>Journal of Physical Chemistry C</i> , 2014 , 118, 19995-20001	3.8	14
181	Ab Initio Optoelectronic Properties of Silicon Nanoparticles: Excitation Energies, Sum Rules, and Tamm-Dancoff Approximation. <i>Journal of Chemical Theory and Computation</i> , 2014 , 10, 3290-8	6.4	19
180	Electronic structure of the silicon vacancy color center in diamond. <i>Physical Review Letters</i> , 2014 , 112, 036405	7.4	225
179	Electrically and mechanically tunable electron spins in silicon carbide color centers. <i>Physical Review Letters</i> , 2014 , 112, 187601	7.4	123
178	Two-site diamond-like point defects as new single-photon emitters. <i>EPJ Web of Conferences</i> , 2014 , 78, 05001	0.3	
177	Publisher's Note: Formation of NV centers in diamond: A theoretical study based on calculated transitions and migration of nitrogen and vacancy related defects [Phys. Rev. B 89, 075203 (2014)]. <i>Physical Review B</i> , 2014 , 89,	3.3	8
176	Electronic and optical properties of pure and modified diamondoids studied by many-body perturbation theory and time-dependent density functional theory. <i>Journal of Chemical Physics</i> , 2014 , 141, 064308	3.9	24
175	Characterization of the nitrogen split interstitial defect in wurtzite aluminum nitride using density functional theory. <i>Journal of Applied Physics</i> , 2014 , 116, 113702	2.5	5
174	Pressure and temperature dependence of the zero-field splitting in the ground state of NV centers in diamond: A first-principles study. <i>Physical Review B</i> , 2014 , 90,	3.3	64
173	Theoretical Investigation of the Single Photon Emitter Carbon Antisite-Vacancy Pair in 4H-SiC. <i>Materials Science Forum</i> , 2014 , 778-780, 495-498	0.4	1
172	Identification of the Negative Carbon Vacancy at Quasi-Cubic Site in 4H-SiC by EPR and Theoretical Calculations. <i>Materials Science Forum</i> , 2014 , 778-780, 285-288	0.4	
171	First Principles Investigation of Divacancy in SiC Polytypes for Solid State Qubit Application. <i>Materials Science Forum</i> , 2014 , 778-780, 499-502	0.4	3
170	Ab initio characterization of a Ni-related defect in diamond: The W8 center. <i>Physical Review B</i> , 2013 , 87,	3.3	10
169	Ab initio study of the split silicon-vacancy defect in diamond: Electronic structure and related properties. <i>Physical Review B</i> , 2013 , 88,	3.3	116
168	Limitations of the hybrid functional approach to electronic structure of transition metal oxides. <i>Physical Review B</i> , 2013 , 88,	3.3	20
167	Hyperfine coupling of point defects in semiconductors by hybrid density functional calculations: The role of core spin polarization. <i>Physical Review B</i> , 2013 , 88,	3.3	61

166	Negative-U carbon vacancy in 4H-SiC: Assessment of charge correction schemes and identification of the negative carbon vacancy at the quasicubic site. <i>Physical Review B</i> , 2013 , 88,	3.3	39
165	High-pressure core structures of Si nanoparticles for solar energy conversion. <i>Physical Review Letters</i> , 2013 , 110, 046804	7.4	56
164	Increasing impact ionization rates in Si nanoparticles through surface engineering: A density functional study. <i>Physical Review B</i> , 2013 , 87,	3.3	23
163	Optically controlled switching of the charge state of a single nitrogen-vacancy center in diamond at cryogenic temperatures. <i>Physical Review Letters</i> , 2013 , 110, 167402	7.4	141
162	Role of screening in the density functional applied to transition-metal defects in semiconductors. <i>Physical Review B</i> , 2013 , 87,	3.3	29
161	Readout and control of a single nuclear spin with a metastable electron spin ancilla. <i>Nature Nanotechnology</i> , 2013 , 8, 487-92	28.7	49
160	Silicon carbide quantum dots for bioimaging. <i>Journal of Materials Research</i> , 2013 , 28, 205-209	2.5	33
159	Optical Properties of the Niobium Centre in 4H, 6H, and 15R SiC. <i>Materials Science Forum</i> , 2013 , 740-742, 405-408	0.4	1
158	Introducing Color Centers to Silicon Carbide Nanocrystals for In Vivo Biomarker Applications: A First Principles Study. <i>Materials Science Forum</i> , 2013 , 740-742, 641-644	0.4	0
157	Preparation of small silicon carbide quantum dots by wet chemical etching. <i>Journal of Materials Research</i> , 2013 , 28, 44-49	2.5	34
156	Optical identification and electronic configuration of tungsten in 4H- and 6H-SiC. <i>Physica B: Condensed Matter</i> , 2012 , 407, 1462-1466	2.8	12
155	Tuning the optical gap of nanometer-size diamond cages by sulfurization: a time-dependent density functional study. <i>Physical Review Letters</i> , 2012 , 108, 267401	7.4	36
154	Electrically driven single-photon source at room temperature in diamond. <i>Nature Photonics</i> , 2012 , 6, 299-303	33.9	248
153	Ab initio study of phosphorus donors acting as quantum bits in silicon nanowires. <i>Nano Letters</i> , 2012 , 12, 3460-5	11.5	6
152	Near-infrared luminescent cubic silicon carbide nanocrystals for in vivo biomarker applications: an ab initio study. <i>Nanoscale</i> , 2012 , 4, 7720-6	7.7	36
151	Identification of defects at the interface between 3C-SiC quantum dots and a SiO ₂ embedding matrix. <i>Physica Status Solidi (B): Basic Research</i> , 2012 , 249, 360-367	1.3	6
150	Anharmonic vibrations of the dicarbon antisite defect in 4H-SiC. <i>Applied Physics Letters</i> , 2012 , 100, 132107	0.4	3
149	Excitation Properties of Silicon Vacancy in Silicon Carbide. <i>Materials Science Forum</i> , 2012 , 717-720, 255-258	2.5	5

148	Electronic Configuration of Tungsten in 4H-, 6H-, and 15R-SiC. <i>Materials Science Forum</i> , 2012 , 717-720, 211-216	0.4	
147	Identification of Niobium in 4H-SiC by EPR and Ab Initio Studies. <i>Materials Science Forum</i> , 2012 , 717-720, 217-220	0.4	3
146	Local Thermal Expansion and the C-C Stretch Vibration of the Dicarbon Antisite in 4H SiC. <i>Materials Science Forum</i> , 2012 , 717-720, 263-266	0.4	1
145	Electron paramagnetic resonance and theoretical studies of Nb in 4H- and 6H-SiC. <i>Journal of Applied Physics</i> , 2012 , 112, 083711	2.5	10
144	Preparation of Small Silicon Carbide Quantum Dots by Wet Chemical Etching. <i>Materials Research Society Symposia Proceedings</i> , 2012 , 1468, 25		
143	Transition Metal Defects in Cubic and Hexagonal Polytypes of SiC: Site Selection, Magnetic and Optical Properties from Ab Initio Calculations. <i>Materials Science Forum</i> , 2012 , 717-720, 205-210	0.4	2
142	Excitation spectrum of point defects in semiconductors studied by time-dependent density functional theory. <i>Journal of Materials Research</i> , 2012 , 27, 897-909	2.5	28
141	Properties of nitrogen-vacancy centers in diamond: the group theoretic approach. <i>New Journal of Physics</i> , 2011 , 13, 025025	2.9	249
140	Defects in SiC: Theory. <i>Materials Science Forum</i> , 2011 , 679-680, 225-232	0.4	4
139	Direct correlation of crystal structure and optical properties in wurtzite/zinc-blende GaAs nanowire heterostructures. <i>Physical Review B</i> , 2011 , 83,	3.3	181
138	Time-Dependent Density Functional Study on the Excitation Spectrum of Point Defects in Semiconductors 2011 , 341-358		
137	¹³ C hyperfine interactions in the nitrogen-vacancy centre in diamond. <i>New Journal of Physics</i> , 2011 , 13, 025021	2.9	90
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